

N-channel 600 V, 1.26 Ω typ., 3.7 A MDmesh II Plus™ low Qg Power MOSFETs in DPAK, TO-220 and IPAK packages

Datasheet - preliminary data

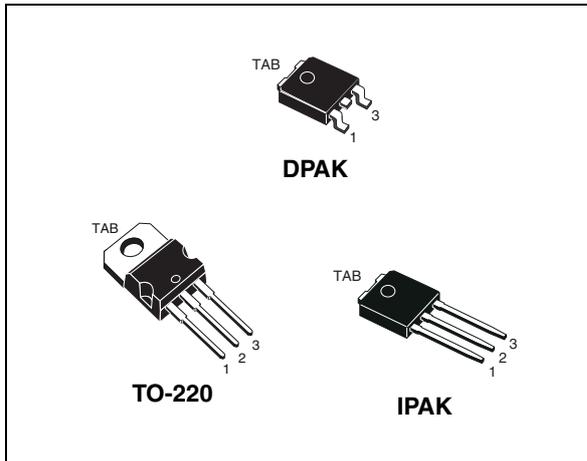
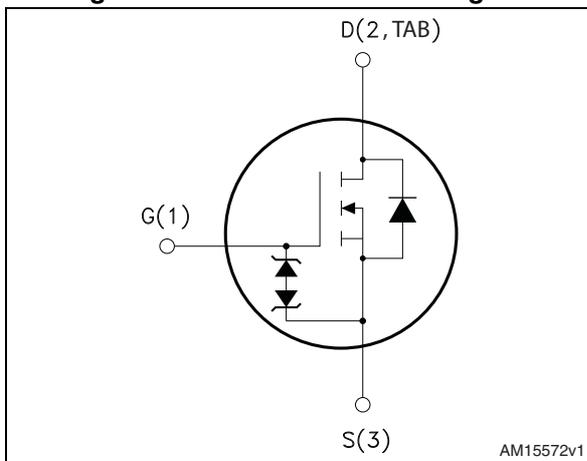


Figure 1. Internal schematic diagram



Features

Order codes	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	I_D
STD5N60M2	650 V	1.4 Ω	3.7 A
STP5N60M2			
STU5N60M2			

- Extremely low gate charge
- Lower $R_{DS(on)}$ x area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using a new generation of MDmesh™ technology: MDmesh II Plus™ low Qg. These revolutionary Power MOSFETs associate a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. They are therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD5N60M2	5N60M2	DPAK	Tape and reel
STP5N60M2		TO-220	Tube
STU5N60M2		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	3.7	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.4	A
$I_{DM}^{(1)}$	Drain current (pulsed)	15	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	45	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	

1. Pulse width limited by safe operating area..
2. $I_{SD} \leq 3.7\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$
3. $V_{DS} \leq 480\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case max	2.08			$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max ⁽¹⁾	50			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max			100	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² FR-4, 2 Oz copper board

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	TBD	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$, $I_D= I_{AR}$; $V_{DD}=50$)	TBD	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.85\text{ A}$		1.26	1.4	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	165	-	pF
C_{oss}	Output capacitance		-	14	-	pF
C_{riss}	Reverse transfer capacitance		-	1	-	pF
$C_{oss\text{ eq.}(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$, $V_{GS} = 0$	-	TBD	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	10	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}$, $I_D = 3.7\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 3)	-	4.5	-	nC
Q_{gs}	Gate-source charge		-	TBD	-	nC
Q_{gd}	Gate-drain charge		-	TBD	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 3.7\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 2 and Figure 7)	-	TBD	-	ns
t_r	Rise time		-	TBD	-	ns
$t_{d(off)}$	Turn-off delay time		-	TBD	-	ns
t_f	Fall time		-	TBD	-	ns

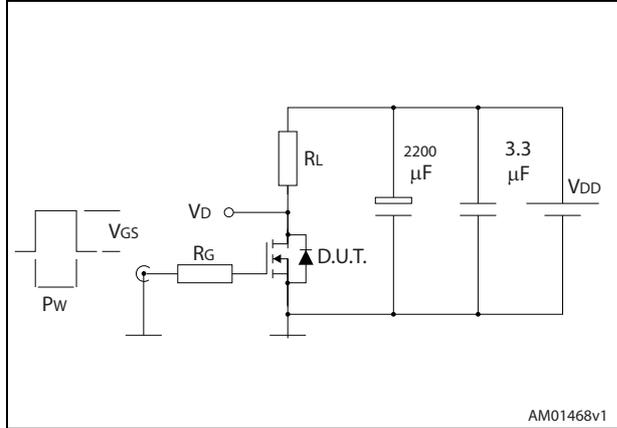
Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		3.7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		15	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 3.7A, V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 3.7 A, di/dt = 100 A/\mu s$ $V_{DD} = 60 V$ (see Figure 4)	-	TBD		ns
Q_{rr}	Reverse recovery charge		-	TBD		μC
I_{RRM}	Reverse recovery current		-	TBD		A
t_{rr}	Reverse recovery time	$I_{SD} = 3.7 A, di/dt = 100 A/\mu s$ $V_{DD} = 60 V, T_j = 150\text{ }^\circ C$ (see Figure 4)	-	TBD		ns
Q_{rr}	Reverse recovery charge		-	TBD		μC
I_{RRM}	Reverse recovery current		-	TBD		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

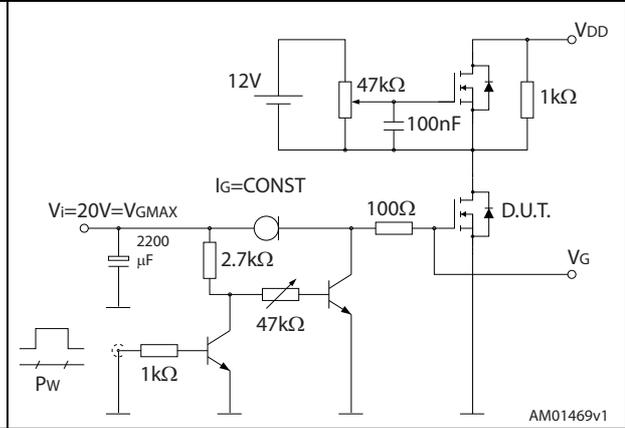
3 Test circuits

Figure 2. Switching times test circuit for resistive load



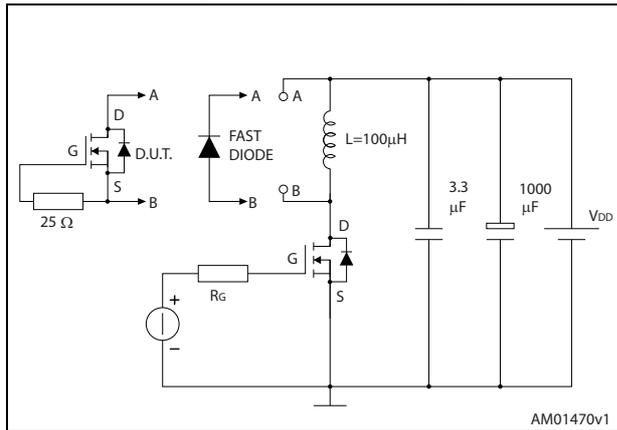
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Figure 3. Gate charge test circuit



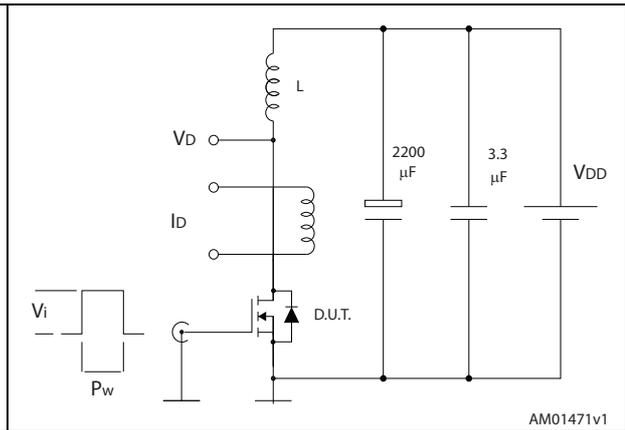
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Figure 4. Test circuit for inductive load switching and diode recovery times



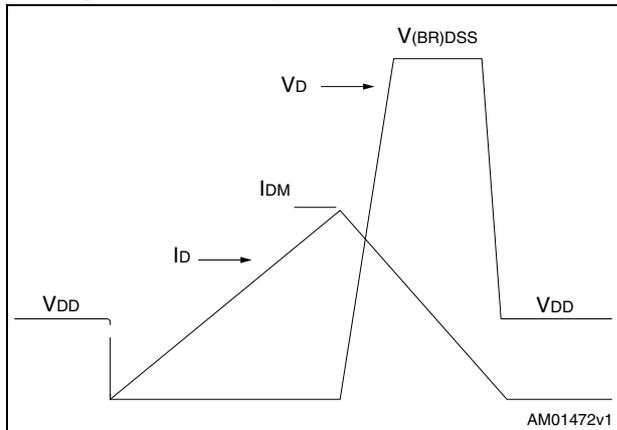
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Figure 5. Unclamped inductive load test circuit



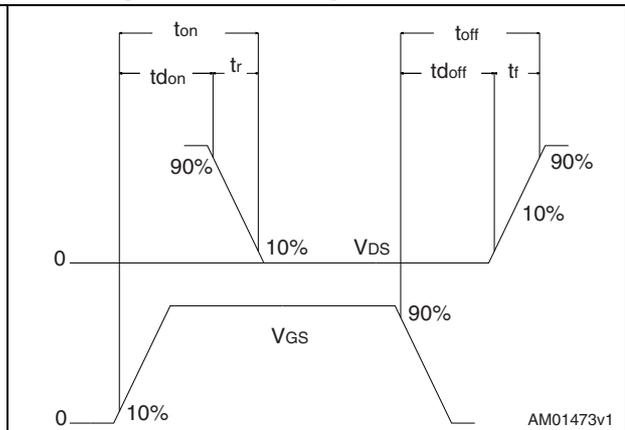
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Figure 6. Unclamped inductive waveform



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Figure 7. Switching time waveform



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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 9. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 8. DPAK (TO-252) type A drawing

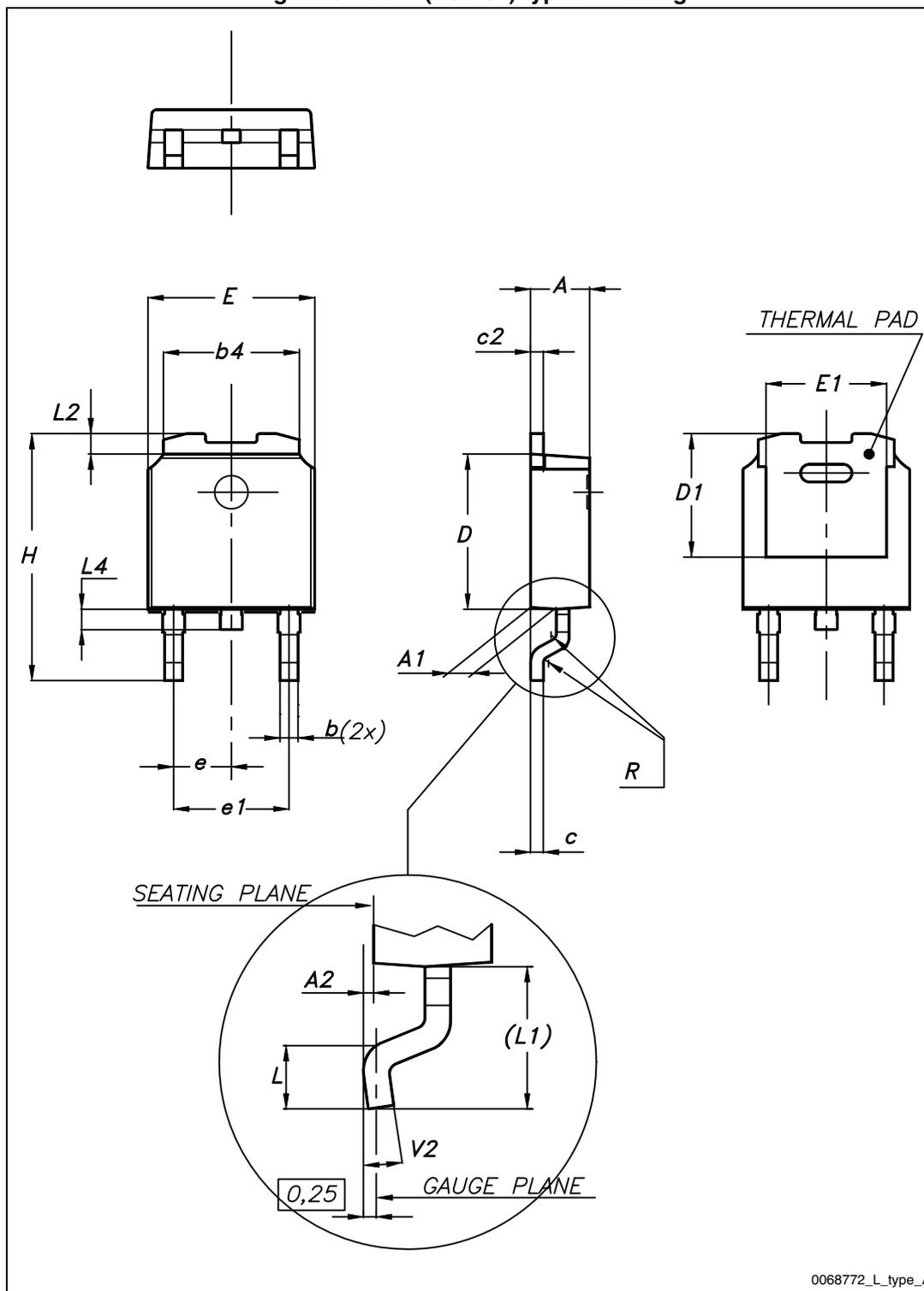
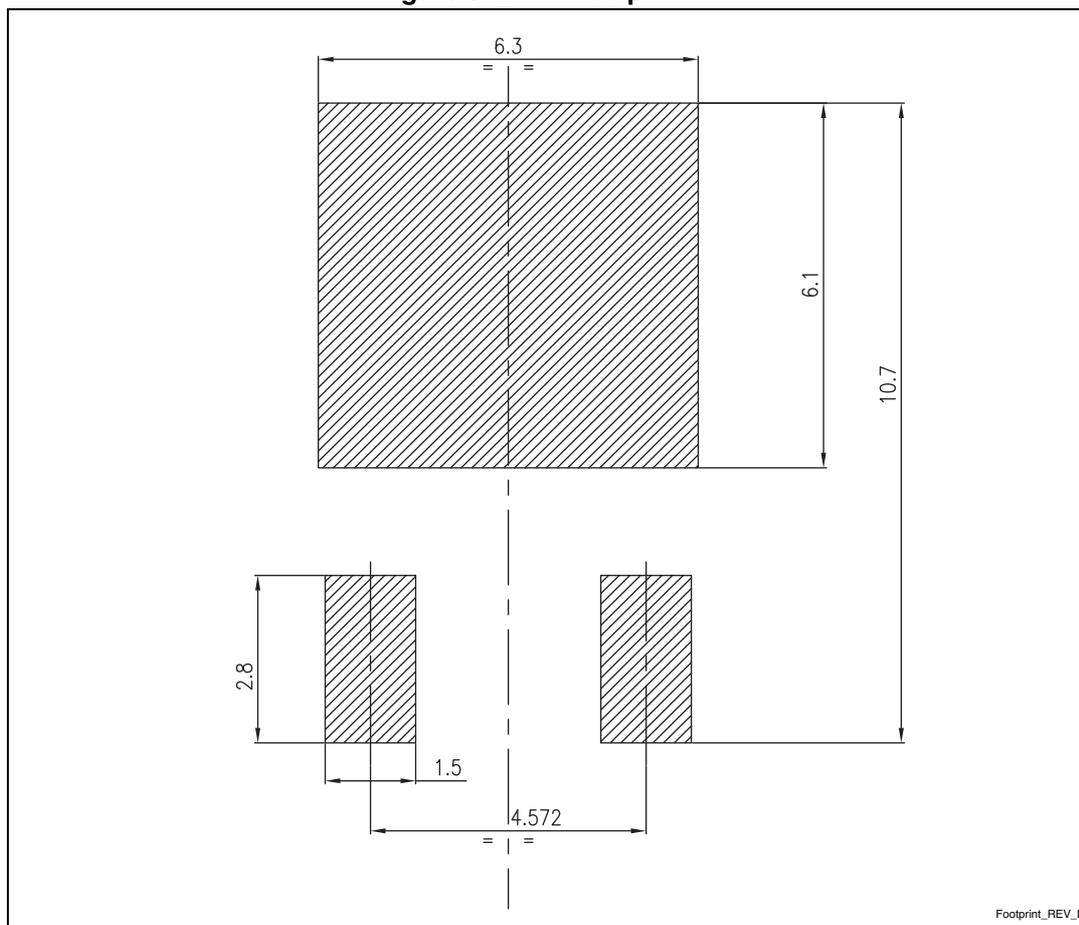


Figure 9. DPAK footprint (a)



Footprint_REV_L

a. All dimensions are in millimeters

Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 10. TO-220 type A drawing

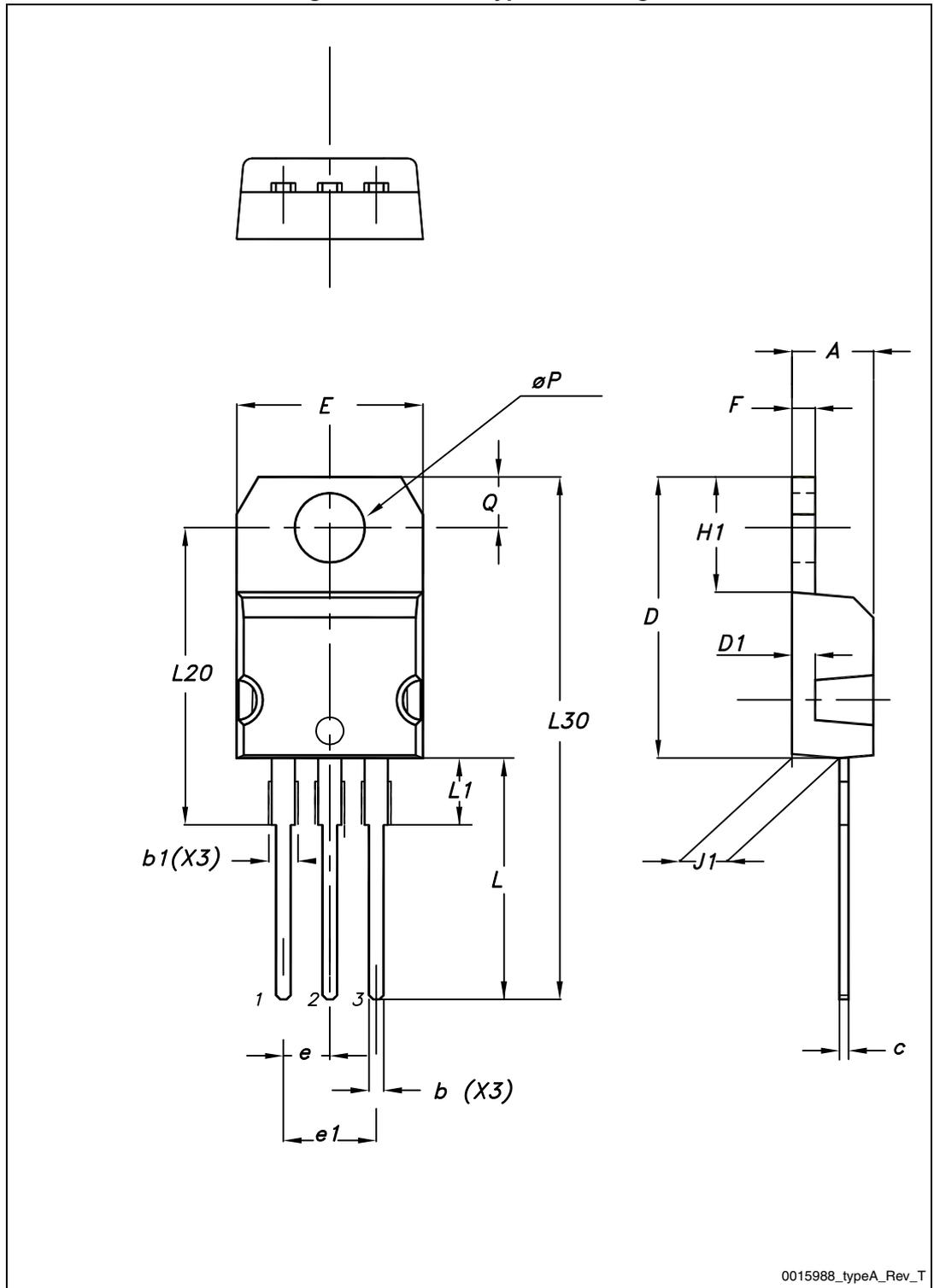
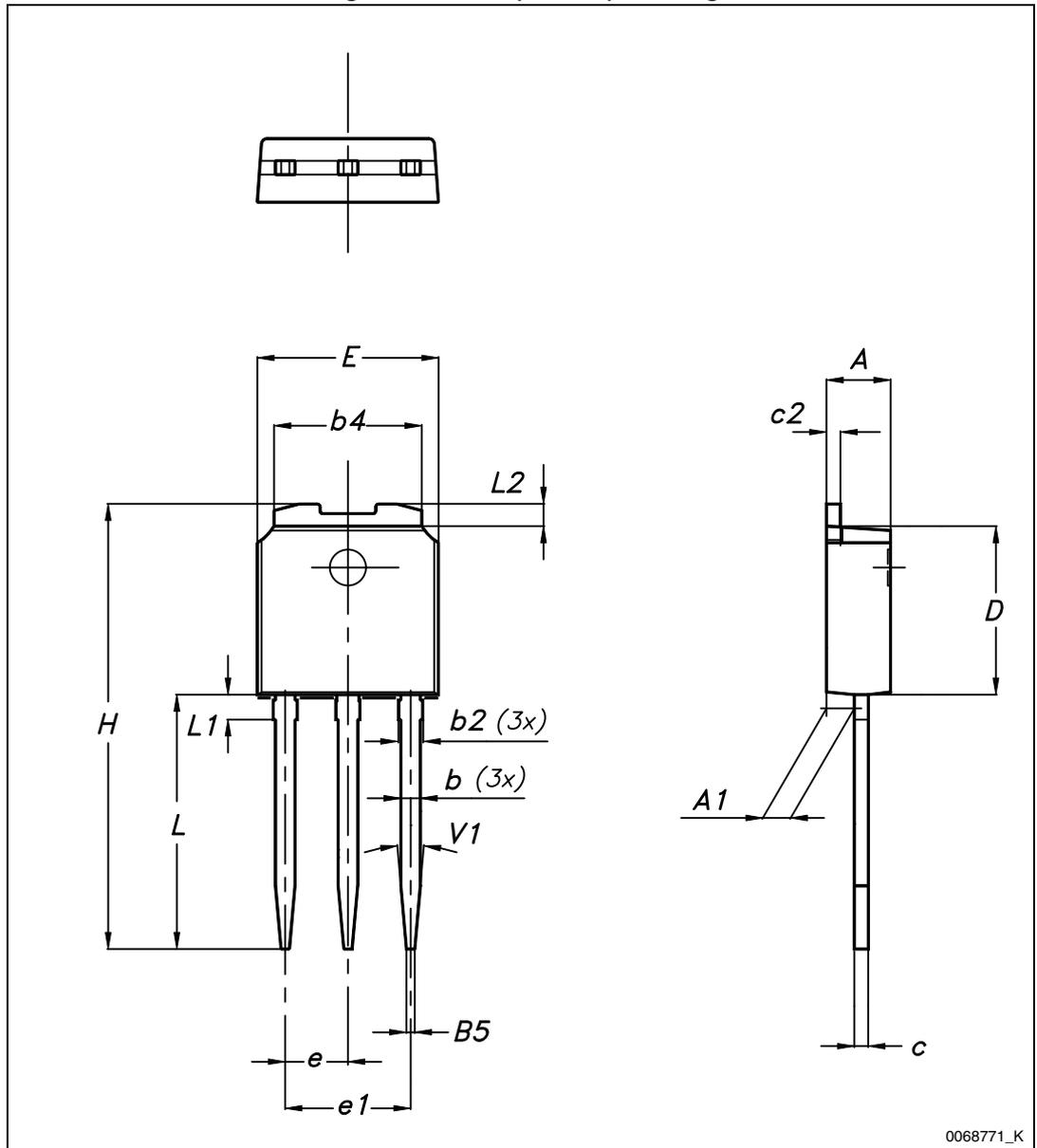


Table 11. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Figure 11. IPAK (TO-251) drawing



5 Packaging mechanical data

Table 12. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 12. Tape

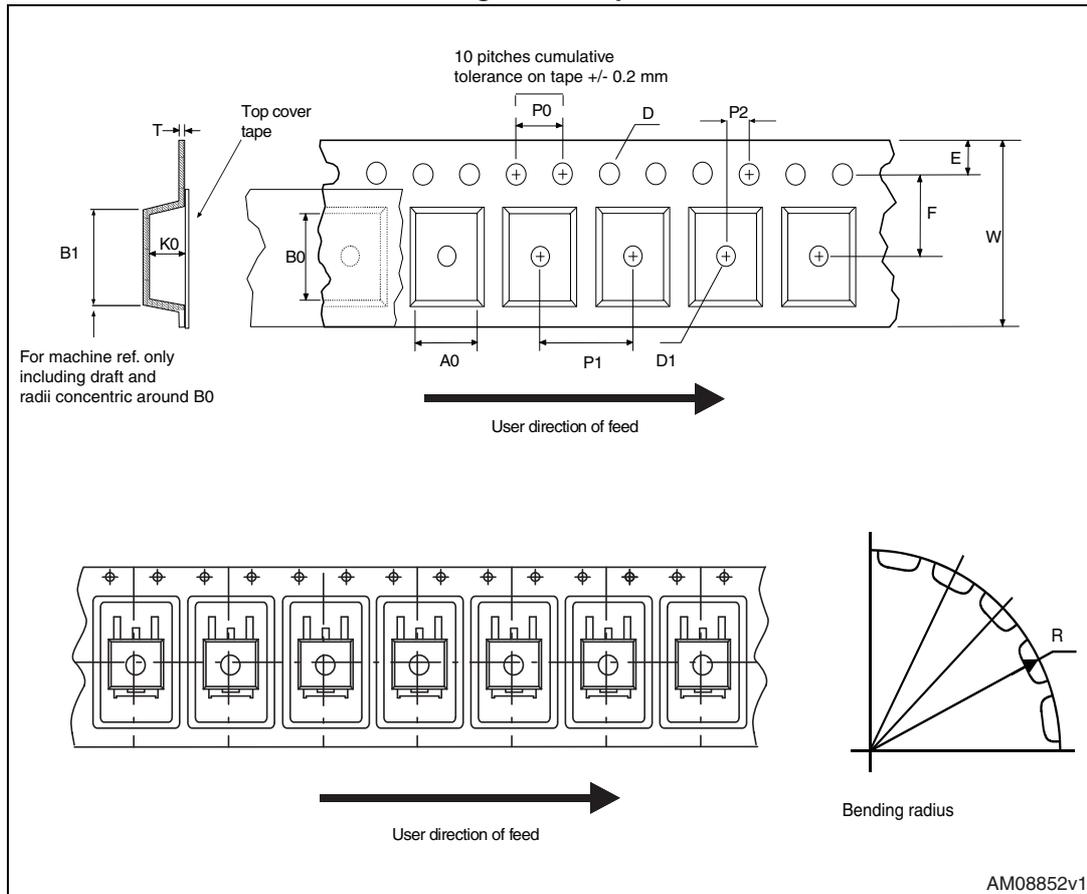
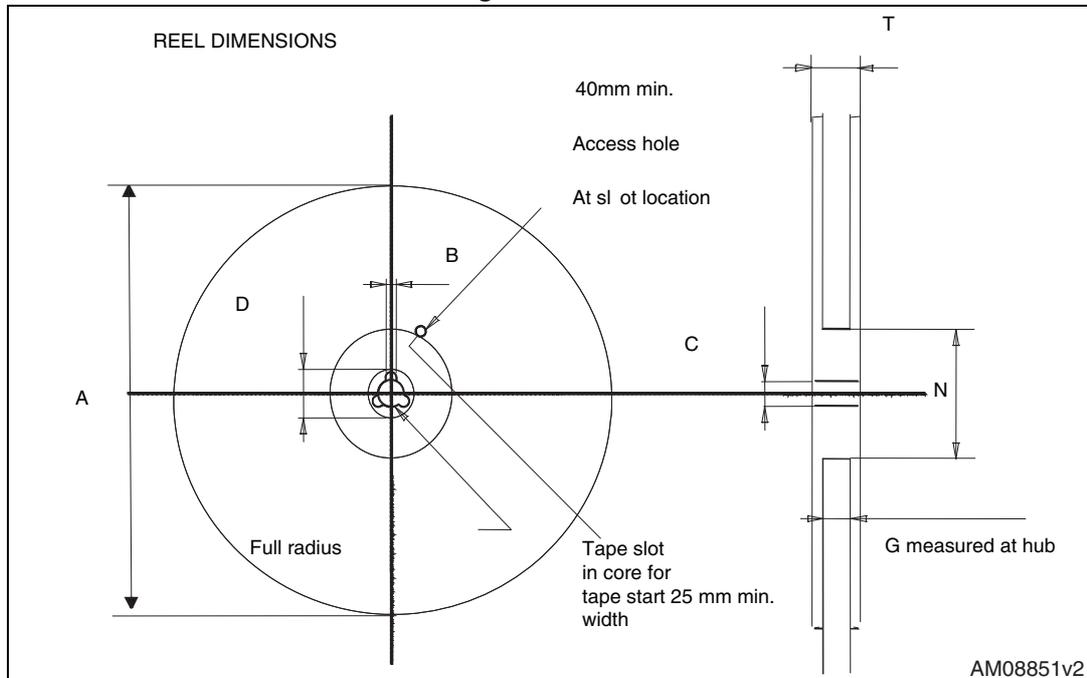


Figure 13. Reel



6 Revision history

Table 13. Document revision history

Date	Revision	Changes
30-Sep-2013	1	First release.

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